

# Atsushi Ogura

## List of Publications by Year in descending order

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papers

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#	ARTICLE	IF	CITATIONS
1	Raman spectra of size-selected silicon clusters and comparison with calculated structures. <i>Nature</i> , 1993, 366, 42-44.	27.8	393
2	Structures and coalescence behavior of size-selected silicon nanoclusters studied by surface-plasmon-polariton enhanced Raman spectroscopy. <i>Journal of Chemical Physics</i> , 1999, 110, 12161-12172.	3.0	87
3	UV-Raman Spectroscopy System for Local and Global Strain Measurements in Si. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 3007-3011.	1.5	85
4	Gas source silicon molecular beam epitaxy using silane. <i>Applied Physics Letters</i> , 1987, 51, 2213-2215.	3.3	80
5	Improvement in ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using ZrO <sub>2</sub> seed layer. <i>Applied Physics Express</i> , 2017, 10, 081501.	2.4	63
6	HfO <sub>2</sub> growth by low-pressure chemical vapor deposition using the Hf(N(C <sub>2</sub> H <sub>5</sub> ) <sub>2</sub> ) <sub>4</sub> /O <sub>2</sub> gas system. <i>Journal of Crystal Growth</i> , 2001, 233, 292-297.	1.5	62
7	Ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films fabricated by 300°C low temperature process with plasma-enhanced atomic layer deposition. <i>Microelectronic Engineering</i> , 2019, 215, 111013.	2.4	55
8	Multi-layered MoS <sub>2</sub> film formed by high-temperature sputtering for enhancement-mode nMOSFETs. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DN08.	1.5	53
9	Using tetrakis-diethylamido-hafnium for HfO <sub>2</sub> thin-film growth in low-pressure chemical vapor deposition. <i>Thin Solid Films</i> , 2002, 406, 215-218.	1.8	46
10	Characterization of Si/GexSi <sub>1-x</sub> structures by micro-Raman imaging. <i>Applied Physics Letters</i> , 2004, 84, 2533-2535.	3.3	46
11	Improvement in ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using top- and bottom-ZrO <sub>2</sub> nucleation layers. <i>APL Materials</i> , 2019, 7, .	5.1	46
12	Analysis of Intra-Grain Defects in Multicrystalline Silicon Wafers by Photoluminescence Mapping and Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L641-L643.	1.5	43
13	Miniaturized planar Si-nanowire micro-thermoelectric generator using exuded thermal field for power generation. <i>Science and Technology of Advanced Materials</i> , 2018, 19, 443-453.	6.1	43
14	Low-temperature redistribution of As in Si during Ni silicide formation. <i>Journal of Applied Physics</i> , 1984, 56, 2725-2728.	2.5	36
15	Low-Carrier-Density Sputtered MoS <sub>2</sub> Film by Vapor-Phase Sulfurization. <i>Journal of Electronic Materials</i> , 2018, 47, 3497-3501.	2.2	36
16	Transverse-optical phonons excited in Si using a high-numerical-aperture lens. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	34
17	Role of i-aSi:H Layers in aSi:H/cSi Heterojunction Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2013, 3, 1149-1155.	2.5	33
18	On the gate-stack origin threshold voltage variability in scaled FinFETs and multi-FinFETs. , 2010, , .		32

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19	Strain-induced transconductance enhancement by pattern dependent oxidation in silicon nanowire field-effect transistors. Applied Physics Letters, 2007, 91, 202117.	3.3	29
20	Photoluminescence Analysis of Iron Contamination Effect in Multicrystalline Silicon Wafers for Solar Cells. Journal of Electronic Materials, 2010, 39, 747-750.	2.2	29
21	Channel strain analysis in high-performance damascene-gate p-metal-oxide-semiconductor field effect transistors using high-spatial resolution Raman spectroscopy. Journal of Applied Physics, 2010, 107, .	2.5	29
22	Interface engineering for the passivation of c-Si with O <sub>3</sub> -based atomic layer deposited AlO <sub>x</sub> for solar cell application. Applied Physics Letters, 2012, 100, .	3.3	29
23	Investigation on antireflection coating for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2014, 53, 03CE01.	1.5	29
24	Nanoscale Wet Etching of Physical-Vapor-Deposited Titanium Nitride and Its Application to Sub-30-nm-Gate-Length Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Fabrication. Japanese Journal of Applied Physics, 2010, 49, 06GH18.	1.5	27
25	Improving crystalline quality of sputtering-deposited MoS <sub>2</sub> thin film by postdeposition sulfurization annealing using (t-C <sub>4</sub> H <sub>9</sub> ) <sub>2</sub> S <sub>2</sub> . Japanese Journal of Applied Physics, 2016, 55, 04EJ07.	1.5	26
26	Quantitative relationship between sputter-deposited-MoS <sub>2</sub> properties and underlying-SiO <sub>2</sub> surface roughness. Applied Physics Express, 2017, 10, 041202.	2.4	26
27	Novel technique for Si epitaxial lateral overgrowth: Tunnel epitaxy. Applied Physics Letters, 1989, 55, 2205-2207.	3.3	25
28	Microscopic and spectroscopic mapping of dislocation-related photoluminescence in multicrystalline silicon wafers. Journal of Materials Science: Materials in Electronics, 2008, 19, 132-134.	2.2	25
29	Positive and negative dipole layer formation at high- $\kappa$ /SiO <sub>2</sub> interfaces simulated by classical molecular dynamics. Japanese Journal of Applied Physics, 2016, 55, 04EB03.	1.5	25
30	Characterization of Strain for High-Performance Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor. Japanese Journal of Applied Physics, 2008, 47, 2538-2543.	1.5	24
31	Evaluation of defects generation in crystalline silicon ingot grown by cast technique with seed crystal for solar cells. Journal of Applied Physics, 2012, 111, 074505.	2.5	24
32	Improvement of SiO <sub>2</sub> /Si Interface Flatness by Postâ€“Oxidation Anneal. Journal of the Electrochemical Society, 1991, 138, 807-810.	2.9	23
33	Defect Analysis in Bonded and H + Split Silicon-on-Insulator Wafers by Photoluminescence Spectroscopy and Transmission Electron Microscopy. Japanese Journal of Applied Physics, 1998, 37, L1199-L1201.	1.5	23
34	A Comparative Study of Nitrogen Gas Flow Ratio Dependence on the Electrical Characteristics of Sputtered Titanium Nitride Gate Bulk Planar Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors and Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2009, 48, 05DC01.	1.5	23
35	Interaction between Metal Impurities and Small-Angle Grain Boundaries on Recombination Properties in Multicrystalline Silicon for Solar Cells. Applied Physics Express, 2012, 5, 042301.	2.4	23
36	Volatile CVD precursor for Ni film: cyclopentadienylallylnickel. Journal of Crystal Growth, 2005, 275, e1115-e1119.	1.5	22

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37	Demonstration of 1200V Scaled IGBTs Driven by 5V Gate Voltage with Superiorly Low Switching Loss. , 2018, , .		21
38	Infrared studies of silicon oxide formation in silicon wafers implanted with oxygen. Applied Physics Letters, 1998, 72, 2853-2855.	3.3	20
39	Annealing properties of defects during Si-on-insulator fabrication by low-dose oxygen implantation studied by monoenergetic positron beams. Journal of Applied Physics, 2000, 87, 1659-1665.	2.5	20
40	Vapor Pressure of Hf and Si Precursors for HfSi <sub>1-x</sub> O <sub>2</sub> Deposition Evaluated by a Saturated Gas Technique. Japanese Journal of Applied Physics, 2004, 43, 966-967.	1.5	20
41	Nitrogen Gas Flow Ratio and Rapid Thermal Annealing Temperature Dependences of Sputtered Titanium Nitride Gate Work Function and Their Effect on Device Characteristics. Japanese Journal of Applied Physics, 2008, 47, 2433.	1.5	20
42	Evaluation of depth profile of defects in ultrathin Si film on buried SiO <sub>2</sub> formed by implanted oxygen. Applied Physics Letters, 1996, 69, 1367-1369.	3.3	19
43	Hf <sub>1-x</sub> Si <sub>x</sub> O <sub>2</sub> deposition by metal organic chemical vapor deposition using the Hf(NEt <sub>2</sub> ) <sub>4</sub> /SiH(NEt <sub>2</sub> ) <sub>3</sub> /O <sub>2</sub> gas system. Thin Solid Films, 2002, 416, 208-211.	1.8	19
44	Formation of a buried oxide film at the damage peak induced by oxygen implantation into a Si substrate. Applied Physics Letters, 1999, 74, 2188-2190.	3.3	18
45	Evaluation of buried oxide formation in low-dose SIMOX process. Applied Surface Science, 2000, 159-160, 104-110.	6.1	18
46	Effects of deposition conditions on step-coverage quality in low-pressure chemical vapor deposition of HfO <sub>2</sub> . Journal of Crystal Growth, 2002, 235, 365-370.	1.5	18
47	Biaxial stress evaluation in GeSn film epitaxially grown on Ge substrate by oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 091301.	1.5	18
48	Measurement of in-plane and depth strain profiles in strained-Si substrates. Solid-State Electronics, 2007, 51, 219-225.	1.4	17
49	High-mobility and low-parasitic resistance characteristics in strained Ge nanowire pMOSFETs with metal source/drain structure formed by doping-free processes. , 2012, , .		17
50	Advantage in solar cell efficiency of high-quality seed cast mono Si ingot. Applied Physics Express, 2015, 8, 062301.	2.4	17
51	Characteristics of Oxide TFT Using Carbon-Doped In <sub>2</sub> O <sub>3</sub> Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (In <sup>TM</sup> -EtCp) and H <sub>2</sub> O & O <sub>3</sub> . ECS Transactions, 2019, 92, 3-13.	0.5	17
52	Improvement in ferroelectricity and breakdown voltage of over 20-nm-thick Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> bilayer by atomic layer deposition. Applied Physics Letters, 2020, 117, .	3.3	17
53	Extension of Dose Window for Low-Dose Separation by Implanted Oxygen. Journal of the Electrochemical Society, 1998, 145, 1735-1737.	2.9	16
54	MOCVD precursors for Ta- and Hf-compound films. Journal of Crystal Growth, 2002, 237-239, 586-590.	1.5	16

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55	Ni Precursor for Chemical Vapor Deposition of NiSi. Japanese Journal of Applied Physics, 2004, 43, 1833-1836.	1.5	16
56	Quantitative analysis of impurities in solar-grade Si by photoluminescence spectroscopy around 20 K. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 792-795.	0.8	16
57	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2015, 54, 08KD12.	1.5	16
58	Properties of single-layer MoS <sub>2</sub> film fabricated by combination of sputtering deposition and post deposition sulfurization annealing using (t-C <sub>4</sub> H <sub>9</sub> ) <sub>2</sub> S <sub>2</sub> . Japanese Journal of Applied Physics, 2016, 55, 06GF01.	1.5	16
59	Improved leakage current properties of ZrO <sub>2</sub> /(Ta/Nb) <sub>x</sub> -Al <sub>2</sub> O <sub>3</sub> /ZrO <sub>2</sub> nanolaminate insulating stacks for dynamic random access memory capacitors. Thin Solid Films, 2018, 655, 48-53.	1.8	16
60	Reduction of contact resistivity by As redistribution during Pd <sub>2</sub> Si formation. Journal of Applied Physics, 1983, 54, 4679-4682.	2.5	15
61	Study of Strain Induction for Metal-Oxide-Semiconductor Field-Effect Transistors using Transparent Dummy Gates and Stress Liners. Japanese Journal of Applied Physics, 2009, 48, 066508.	1.5	15
62	Study of the Degradation of p-n Diode Characteristics Caused by Small-Angle Grain Boundaries in Multi-Crystalline Silicon Substrate for Solar Cells. Japanese Journal of Applied Physics, 2009, 48, 121202.	1.5	15
63	Channel-Stress Enhancement Characteristics for Scaled pMOSFETs by Using Damascene Gate With Top-Cut Compressive Stress Liner and eSiGe. IEEE Transactions on Electron Devices, 2009, 56, 2778-2784.	3.0	15
64	Synthesis, characterization and application of intracellular Ag/AgCl nanohybrids biosynthesized in Scenedesmus sp. as neutral lipid inducer and antibacterial agent. Environmental Research, 2021, 201, 111499.	7.5	15
65	Precise Measurement of Strain Induced by Local Oxidation in Thin Silicon Layers of Silicon-on-Insulator Structures. Japanese Journal of Applied Physics, 1998, 37, 1282-1284.	1.5	14
66	In- and out-diffusion of oxygen during the buried-oxide formation in oxygen-implanted silicon. Journal of Applied Physics, 2000, 87, 7782-7787.	2.5	14
67	HfO <sub>2</sub> and Hf <sub>1-x</sub> Si <sub>x</sub> O <sub>2</sub> Thin Films Grown by Metal-Organic CVD Using Tetrakis(diethylamido)hafnium. Chemical Vapor Deposition, 2006, 12, 130-135.	1.3	14
68	Transconductance enhancement of nanowire field-effect transistors by built-up stress induced during thermal oxidation. Applied Physics Letters, 2007, 91, .	3.3	14
69	Evaluation of super-critical thickness strained-Si on insulator (sc-SSOI) substrate. Solid-State Electronics, 2008, 52, 1845-1848.	1.4	14
70	Microscopic Distributions of Light Elements and Their Precipitates in Multicrystalline Silicon for Solar Cells. Japanese Journal of Applied Physics, 2010, 49, 110202.	1.5	14
71	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	3.0	14
72	Butterfly-shaped distribution of SiN precipitates in multi-crystalline Si for solar cells. Journal of Crystal Growth, 2013, 377, 37-42.	1.5	14

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73	Minority Carrier Recombination Properties of Crystalline Defect on Silicon Surface Induced by Plasma Enhanced Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2016, 5, Q253-Q256.	1.8	14
74	Effects of Aluminum in Metallization Paste on the Electrical Losses in Bifacial N-type Crystalline Silicon Solar Cells. Energy Procedia, 2016, 98, 106-114.	1.8	14
75	Low-temperature grain growth of initially ~100% textured polycrystalline silicon films amorphized by silicon ion implantation with normal incident angle. Journal of Applied Physics, 1986, 59, 289-291.	2.5	13
76	Crystallinity estimation of thin silicon-on-insulator layers by means of diffractometry using a highly parallel X-ray microbeam. Journal of Synchrotron Radiation, 2006, 13, 373-377.	2.4	13
77	Evaluation of Anisotropic Strain Relaxation in Strained Silicon-on-Insulator Nanostructure by Oil-Immersion Raman Spectroscopy. Japanese Journal of Applied Physics, 2012, 51, 02BA03.	1.5	13
78	GeSn Film Deposition Using Metal Organic Chemical Vapor Deposition. ECS Transactions, 2013, 53, 245-250.	0.5	13
79	Low-pressure chemical vapor deposition of TaCN films by pyrolysis of ethylamido-tantalum. Journal of Crystal Growth, 2000, 220, 604-609.	1.5	12
80	Formation of patterned buried insulating layer in Si substrates by He <sup>+</sup> implantation and annealing in oxidation atmosphere. Applied Physics Letters, 2003, 82, 4480-4482.	3.3	12
81	Depth profiling of strain and defects in Si <sup>1-x</sup> Ge <sup>x</sup> Si heterostructures by micro-Raman imaging. Journal of Applied Physics, 2006, 100, 073511.	2.5	12
82	Mobility and Velocity Enhancement Effects of High Uniaxial Stress on Si (100) and (110) Substrates for Short-Channel pFETs. IEEE Transactions on Electron Devices, 2010, 57, 1295-1300.	3.0	12
83	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n <sup>+</sup> -Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	1.5	12
84	Investigation of Phonon Deformation Potentials in Si <sub>1-x</sub> Ge <sub>x</sub> by Oil-Immersion Raman Spectroscopy. Applied Physics Express, 2012, 5, 111301.	2.4	12
85	Variability Analysis of Scaled Crystal Channel and Poly-Si Channel FinFETs. IEEE Transactions on Electron Devices, 2012, 59, 573-581.	3.0	12
86	Evaluation of Sputtering Deposited 2-Dimensional MoS <sub>2</sub> Film by Raman Spectroscopy. Materials Research Society Symposia Proceedings, 2015, 1781, 11-16.	0.1	12
87	Large Scale Uniformity of Sputtering Deposited Single- and Few-Layer MoS <sub>2</sub> Investigated by XPS Multipoint Measurements and Histogram Analysis of Optical Contrast. ECS Journal of Solid State Science and Technology, 2016, 5, Q3012-Q3015.	1.8	12
88	Role of High-k Interlayer in ZrO <sub>2</sub> /High-k/ZrO <sub>2</sub> Insulating Multilayer on Electrical Properties for DRAM Capacitor. ECS Transactions, 2016, 75, 667-674.	0.5	12
89	Effects of thermal budget in n-type bifacial solar cell fabrication processes on effective lifetime of crystalline silicon. AIP Advances, 2017, 7, .	1.3	12
90	Quantification of C in Si by photoluminescence at liquid N temperature after electron irradiation. Applied Physics Express, 2017, 10, 046602.	2.4	12

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91	Determination of phonon deformation potentials and strain-shift coefficients in Ge-rich Si <sub>1-x</sub> Ge <sub>x</sub> crystals and oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 106601.	1.5	12
92	Evaluation of Strained-Silicon by Electron Backscattering Pattern Measurement: Comparison Study with UV-Raman Measurement and Edge Force Model Calculation. Japanese Journal of Applied Physics, 2011, 50, 010111.	1.5	12
93	Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Film Fabrication by Tellurization of Chemical Vapor Deposited GeSb. Japanese Journal of Applied Physics, 2013, 52, 128006.	1.5	11
94	Evaluation of Anisotropic Biaxial Stress in Si <sub>1-x</sub> Ge <sub>x</sub> /Ge Mesa-Structure by Oil-Immersion Raman Spectroscopy. ECS Transactions, 2015, 66, 39-45.	0.5	11
95	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. ACS Applied Nano Materials, 2018, 1, 915-921.	5.0	11
96	Oxygen-related defects and their annealing behavior in low-dose Separation-by-Implanted OXYgen (SIMOX) wafers studied by slow positron beams. Applied Surface Science, 2002, 194, 112-115.	6.1	10
97	Evaluation and Control of Strain in Si Induced by Patterned SiN Stressor. Electrochemical and Solid-State Letters, 2009, 12, H117.	2.2	10
98	Evaluation of local strain in Si using UV-Raman spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 206-211.	3.5	10
99	Evaluation of Strained-Silicon by Electron Backscattering Pattern Measurement: Comparison Study with UV-Raman Measurement and Edge Force Model Calculation. Japanese Journal of Applied Physics, 2011, 50, 010111.	1.5	10
100	Demonstration of Split-Gate Type Trigate Flash Memory With Highly Suppressed Over-Erase. IEEE Electron Device Letters, 2012, 33, 345-347.	3.9	10
101	Ge <sub>1-x</sub> Sn <sub>x</sub> Epitaxial Growth on Ge Substrate by MOCVD. ECS Transactions, 2014, 64, 697-701.	0.5	10
102	Investigation of dislocations in Nb-doped SrTiO <sub>3</sub> by electron-beam-induced current and transmission electron microscopy. Applied Physics Letters, 2015, 106, 102109.	3.3	10
103	MOCVD of Monolayer MoS <sub>2</sub> using Novel Molybdenum Precursor i-Pr <sub>2</sub> DADMo(CO) <sub>3</sub> . MRS Advances, 2018, 3, 379-384.	0.9	10
104	Sputter-Deposited-MoS <sub>2</sub> MISFETs With Top-Gate and Al <sub>2</sub> O <sub>3</sub> Passivation Under Low Thermal Budget for Large Area Integration. IEEE Journal of the Electron Devices Society, 2018, 6, 1246-1252.	2.1	10
105	Control of dipole properties in high-k and SiO <sub>2</sub> stacks on Si substrates with tricolor superstructure. Applied Physics Letters, 2018, 113, .	3.3	10
106	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. Solar Energy, 2019, 188, 1292-1297.	6.1	10
107	Anomalous low energy phonon dispersion in bulk silicon-germanium observed by inelastic x-ray scattering. Applied Physics Letters, 2020, 116, .	3.3	10
108	Germanium film on SiO <sub>2</sub> with a ~100% texture deposited by the rf sputtering technique. Applied Physics Letters, 1985, 47, 1059-1061.	3.3	9

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109	Defects in silicon-on-insulator wafers and their hydrogen interaction studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2002, 91, 6488.	2.5	9
110	Ni Thin Film Deposition from Tetrakis(trifluorophosphine)-Nickel. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L315-L317.	1.5	9
111	Evaluation of Strain in Si-on-Insulator Substrate Induced by Si <sub>3</sub> N <sub>4</sub> Capping Film. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 1465-1468.	1.5	9
112	Improvement of CVD SiO <sub>2</sub> by Post Deposition Microwave Plasma Treatment. <i>ECS Transactions</i> , 2009, 19, 45-51.	0.5	9
113	Quantitative Analysis of Stress Relaxation in Transmission Electron Microscopy Samples by Raman Spectroscopy with a High-Numerical Aperture Lens. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA06.	1.5	9
114	Stress evaluation in thin strained-Si film by polarized Raman spectroscopy using localized surface plasmon resonance. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	9
115	Synchrotron X-ray topography of supercritical-thickness strained silicon-on-insulator wafers for crystalline quality evaluation and electrical characterization using back-gate transistors. <i>Current Applied Physics</i> , 2012, 12, S69-S74.	2.4	9
116	Donor-acceptor pair luminescence in B and P compensated Si co-doped with Ga. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	9
117	Growth of Ge Homoepitaxial Films by Metal-Organic Chemical Vapor Deposition Using t-C <sub>4</sub> H <sub>9</sub> GeH <sub>3</sub> . <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P152-P154.	1.8	9
118	Determination of low carbon concentration in Czochralski-grown Si crystals for solar cells by luminescence activation using electron irradiation. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 070305.	1.5	9
119	Origin of room-temperature photoluminescence around C-line in electron-irradiated Si and its applicability for quantification of carbon. <i>Applied Physics Express</i> , 2018, 11, 041301.	2.4	9
120	Ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> Thin Films Fabricated Using TiN Stressor and ZrO <sub>2</sub> Nucleation Techniques. <i>ECS Transactions</i> , 2018, 86, 31-38.	0.5	9
121	Correlation between ferroelectricity and ferroelectric orthorhombic phase of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using synchrotron x-ray analysis. <i>APL Materials</i> , 2021, 9, .	5.1	9
122	Improvement of Ferroelectricity and Fatigue Property of Thicker Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> /ZrO <sub>2</sub> Bi-layer. <i>ECS Transactions</i> , 2020, 98, 63-70.	0.5	9
123	Impact of Light-Element Impurities on Crystalline Defect Generation in Silicon Wafer. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BP08.	1.5	9
124	Characterization of surface imperfections of silicon-on-insulator wafers by means of extremely asymmetric x-ray reflection topography. <i>Applied Physics Letters</i> , 1996, 68, 693-695.	3.3	8
125	Depth profiles of As and B implanted into Si-on-insulator substrates. <i>Thin Solid Films</i> , 2001, 397, 56-62.	1.8	8
126	Formation of Buried Oxide Layer in Si Substrates by Oxygen Precipitation at Implantation Damage of Light Ions. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L1075-L1077.	1.5	8



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127	Evaluation of HfO <sub>2</sub> film structures deposited by metal-organic chemical vapor deposition using Hf(N(C <sub>2</sub> H <sub>5</sub> ) <sub>2</sub> ) <sub>4</sub> /O <sub>2</sub> gas system. <i>Thin Solid Films</i> , 2003, 441, 161-164.	1.8	8
128	Tris-diethylamino-silane Decomposition due to Tetrakis-diethylamido-hafnium in Hf <sub>1-x</sub> Si <sub>x</sub> O <sub>2</sub> Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L578-L580.	1.5	8
129	Characterization of strained Si wafers by X-ray diffraction techniques. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 189-193.	2.2	8
130	Chemical Vapor Deposition of GeSbTe Thin Films for Next-Generation Phase Change Memory. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 05FF06.	1.5	8
131	Evaluation of Anisotropic Biaxial Stress by Raman Spectroscopy with a High Numerical Aperture Immersion Objective Lens. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DA21.	1.5	8
132	Complementary Distribution of NN and NNO Complexes in Cast-Grown Multicrystalline Silicon for Photovoltaic Cells. <i>Applied Physics Express</i> , 2011, 4, 115601.	2.4	8
133	Electrical field analysis of metal surface plasmon resonance using a biaxially strained Si substrate. <i>Journal of Raman Spectroscopy</i> , 2014, 45, 414-417.	2.5	8
134	Ge incorporated epitaxy of (110) rutile TiO <sub>2</sub> on (100) Ge single crystal at low temperature by pulsed laser deposition. <i>Thin Solid Films</i> , 2015, 591, 105-110.	1.8	8
135	Examination of phonon deformation potentials for accurate strain measurements in silicon-germanium alloys with the whole composition range by Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 026602.	1.5	8
136	Improvement of smooth surface of RuO <sub>2</sub> bottom electrode on Al <sub>2</sub> O <sub>3</sub> buffer layer and characteristics of RuO <sub>2</sub> /TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> /RuO <sub>2</sub> capacitors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	2.1	8
137	Evaluation of Laterally Graded Silicon Germanium Wires for Thermoelectric Devices Fabricated by Rapid Melting Growth. <i>ECS Transactions</i> , 2018, 86, 87-93.	0.5	8
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